

Self-Oscillating Half-Bridge Driver

Features

- Floating channel designed for bootstrap operation
- Integrated 600 V half-bridge gate driver
- 15.6 V zener clamp on Vcc
- True micropower start up
- Tighter initial dead time control
- Low temperature coefficient dead time
- Shutdown feature (1/6th Vcc) on CT pin
- Increased undervoltage lockout Hysteresis (1 V)
- Lower power level-shifting circuit
- Constant LO, HO pulse widths at startup
- Lower di/dt gate driver for better noise immunity
- Low side output in phase with RT
- Excellent latch immunity on all inputs and outputs
- ESD protection on all leads

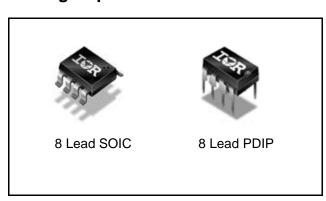
Product Summary

Voffset	600 V max.
Duty Cycle	50%
T_r / T_f	80 ns / 40 ns
V_{CLAMP}	15.6 V
Dead time (typ.)	1.2 μs
lo+/lo- (typ.)	180 mA / 260 mA

Description

The IR25603(S) incorporates a high voltage half-bridge gate driver with a front end oscillator similar to the industry standard CMOS 555 timer. A shutdown feature has been designed into the CT pin, so that both gate driver outputs can be disabled using a low voltage control signal. In addition, the gate driver output pulse widths are the same once the rising undervoltage lockout threshold on Vcc has been reached, resulting in a more stable profile of frequency vs time at startup. Special attention has been paid to maximizing the latch immunity of the device and providing comprehensive ESD protection on all pins.

Package Options



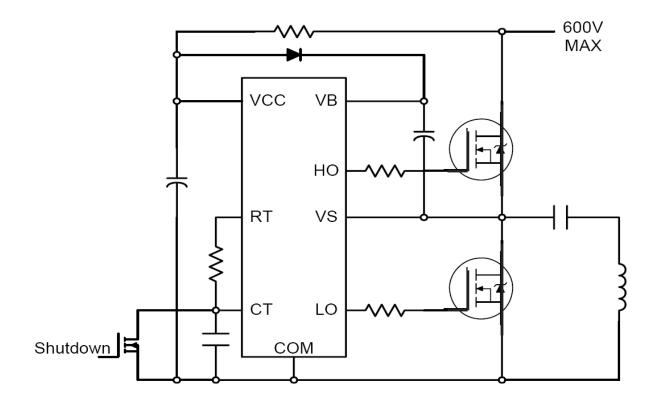
Ordering Information

Danie Bard Namel an	Package Type	Standar	d Pack	On law I I Port Name I are
Base Part Number	r ackage Type	Form	Quantity	Orderable Part Number
IR25603SPBF	SO8N	Tube	95	IR25603SPBF
IR25603SPBF	SO8N	Tape and Reel	2500	IR25603STRPBF
IR25603PBF	PDIP8	Tube	50	IR25603PBF

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Typical Connection Diagram





Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Definition			Units
V _B	High side floating absolute voltage		-0.3	625	
Vs	High side floating supply offset voltage	9	V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage		V _S - 0.3	V _B + 0.3	
V _{LO}	Low side output voltage		-0.3	V _{CC} + 0.3	7 V
V _{RT}	R _T pin voltage		-0.3	V _{CC} + 0.3	
V _{CT}	C _T pin voltage		-0.3	V _{CC} + 0.3	
Icc	Supply current†		_	25	A
I _{RT}	R _T pin current			5	mA
dVs/dt	Allowable offset supply voltage transic	ent	_	50	V/ns
D-	Package power dissipation @ TA ≤	8 lead PDIP	_	1	W
P_{D}	+25°C	8 lead SOIC	_	0.625	VV
D4h	Thermal resistance, junction to	8 lead PDIP	_	125	°C/W
Rth_JA	ambient 8 lead SOIC	8 lead SOIC	_	200	C/VV
TJ	Junction temperature		_	150	_
T _S	Storage temperature		-55	150	°C
TL	Lead temperature (soldering, 10 seco	nds)	_	300	

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply absolute voltage	V _{CC} – 0.7	V_{CLAMP}	
Vs	Steady state high side floating supply offset voltage	††	600	V
Vcc	Supply voltage	10	V_{CLAMP}	
Icc	Supply current	+++	5	mA
T _A	Ambient temperature	-40	125	°C

[†] This IC contains a zener clamp structure between the chip V_{CC} and COM which has a nominal breakdown voltage of 15.6V. Please note that this supply pin should not be driven by a DC, low impedance power source greater than the V_{CLAMP} specified in the Electrical Characteristics section.

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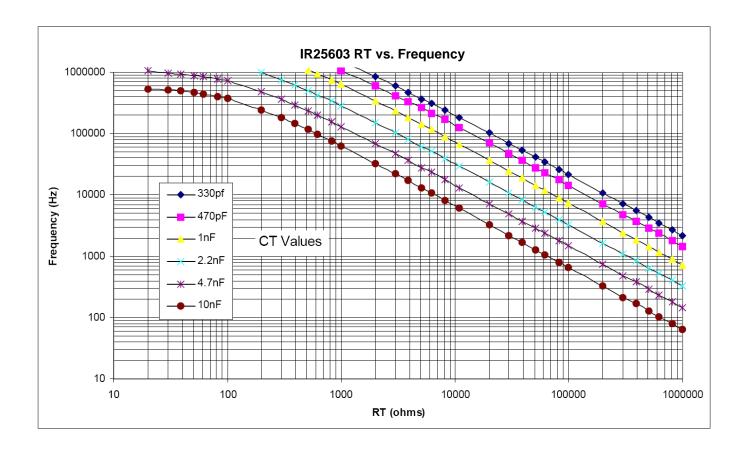
^{††} Care should be taken to avoid output switching conditions where the VS node flies inductively below ground by more than 5V.

^{†††} Enough current should be supplied to the V_{CC} pin of the IC to keep the internal 15.6V zener diode clamping the voltage at this pin.



Recommended Component Values

Symbol	Component	Min.	Max.	Units
R _T	Timing resistor value	10	_	kΩ
C _T	C _T pin capacitor value	330		pF





Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 12V, CL = 1000 pF, CT = 1nF and T_A = 25°C unless otherwise specified.

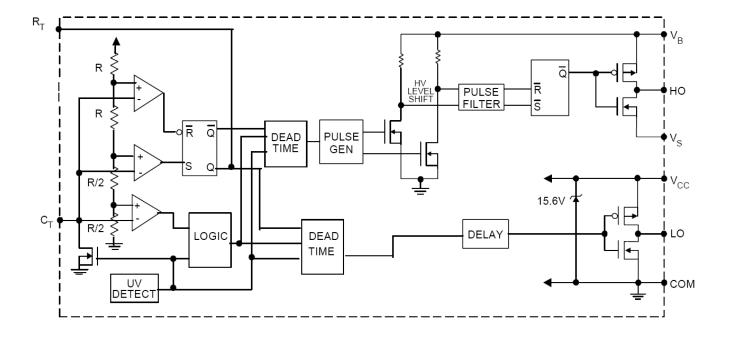
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{CCUV+}	V _{CC} supply undervoltage positive going threshold	8.1	9.0	9.9		
V _{CCUV} -	V _{CC} supply undervoltage negative going threshold	7.2	8.0	8.8	V	
V _{CCUVH}	V _{CC} undervoltage hysteresis	0.5	1.0	1.5		
I _{QCCUV}	Micropower startup V _{CC} supply current	_	75	150	μΑ	V _{CC} ≤ V _{CCUV-}
I _{QCC}	Quiescent V _{CC} supply current		500	950		
VCLAMP	V _{CC} zener clamp voltage	14.4	15.6	16.8	V	$I_{CC} = 5mA$
Floating S	upply Characteristics					
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
I _{QBSUV}	Micropower startup V _{BS} supply current	_	0	10	μA	V _{CC} ≤ V _{CCUV} -
I _{QBS}	Quiescent V _{BS} supply current	_	30	50		
V _{BSMIN}	Minimum required V _{BS} voltage for proper functionality from R _T to HO	_	4.0	5.0	V	$V_{CC} = V_{CCUV+} + 0.1V$
I _{LK}	Offset supply leakage current	_	_	50	μΑ	$V_{B} = V_{S} = 600V$
	I/O Characteristics	84:	T	84	I I I I I I I	Tank Canaditions
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
fosc	Oscillator frequency	19.4	20	20.6	kHz	$R_T = 36.9k\Omega$
	· · ·	94	100	106		$R_T = 7.43k\Omega$
d	R _T pin duty cycle	48	50	52	%	f _O < 100kHz
I _{CT}	C _T pin current		0.001	1.0	μΑ	
I _{CTUV}	UV-mode C _T pin pull down current	0.3	0.7	1.2	mA	$V_{CC} = 7V$
V _{CT+}	Upper C _T ramp voltage threshold	_	8	_	- , , , , , , , , , , , , , , , , , , ,	
V _{CT} -	Lower C _T ramp voltage threshold		4		V	
V _{CTSD}	C _T voltage shutdown threshold	1.8	2.1	2.4		
V_{RT+}	High-level R _T output voltage, V _{CC} -		100	300	_	I _{RT} = 100 μA
	V _{RT}		10	50		I _{RT} = 100 μA
$V_{RT ext{-}}$	Low-level R _T output voltage	_	100	300	mV	I _{RT} = 1mA
VRI-			0	100] '''V	V _{CC} ≤ V _{CCUV} -
	UV-mode R _T output voltage					
V _{RTUV}	UV-mode R_T output voltage SD-Mode R_T output voltage, V_{CC} - V_{RT}	_	10	50		I _{RT} = 100 μA, V _{CT} = 0V



Electrical Characteristics (cont.)

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
VOH	High level output voltage, V _{BIAS} -V _O	_	0	100		$I_O = 0A$
VOL	Low-level output voltage, V _O	_	0	100	mV -	$I_O = 0A$
VOL_UV	UV-mode output voltage, V _O	_	0	100		$I_{O} = 0A$ $V_{CC} \le V_{CCUV}$
t _r	Output rise time	_	80	150		
t _f	Output fall time	_	45	100	ns	
t _{sd}	Shutdown propagation delay	_	660	_		
t _d	Output dead time (HO or LO)	0.75	1.20	1.65	μS	
I _{O+}	Output source current	_	180	_	m A	
I _O -	Output sink current	_	260	_	mA -	

Functional Block Diagram

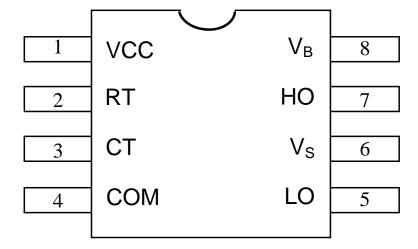




Lead Definitions

Symbol	Description
V _{CC}	Logic and internal gate drive supply voltage
R _T	Oscillator timing resistor input
Ст	Oscillator timing capacitor input
COM	IC power and signal ground
LO	Low side gate driver output
V _S	High voltage floating supply return
НО	High side gate driver output
V _B	High side gate driver floating supply

Lead Assignments





Application Information and Additional Details

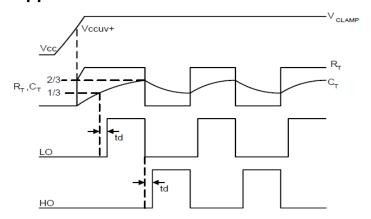


Figure 1. Input/Output Timing Diagram

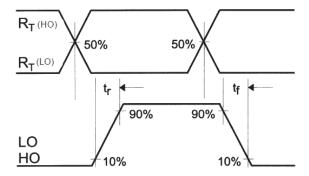


Figure 2. Switching Time Waveform Definitions

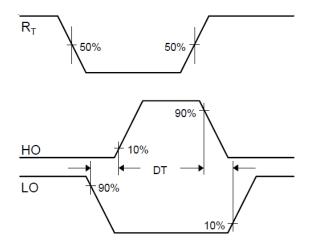
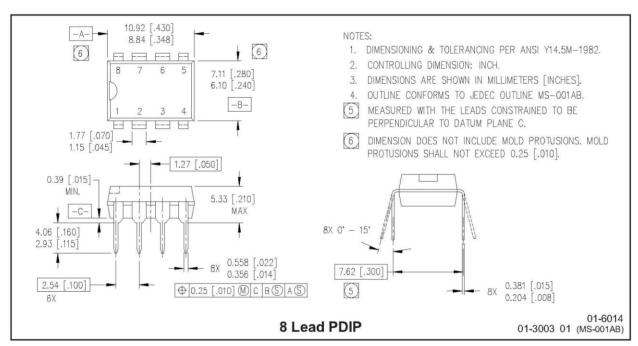
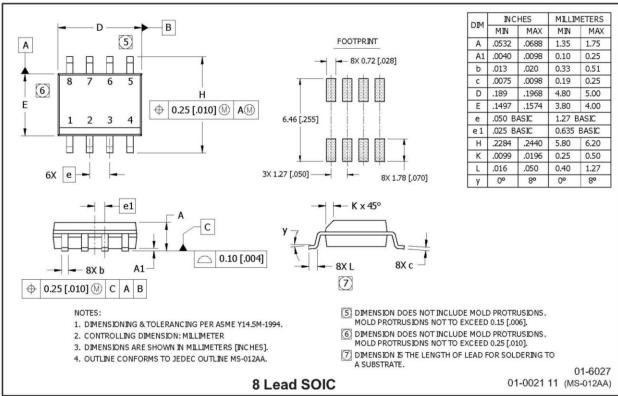


Figure 3. Deadtime Waveform Definitions



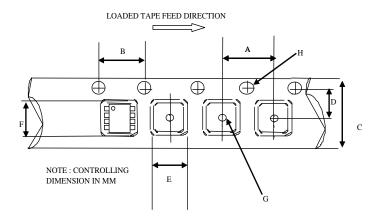
Package Details





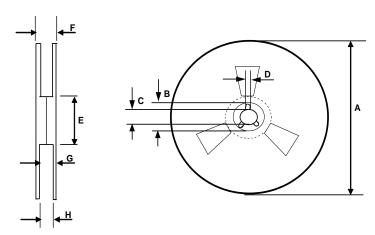


Tape and Reel Details, SO8N



CARRIER TAPE DIMENSION FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

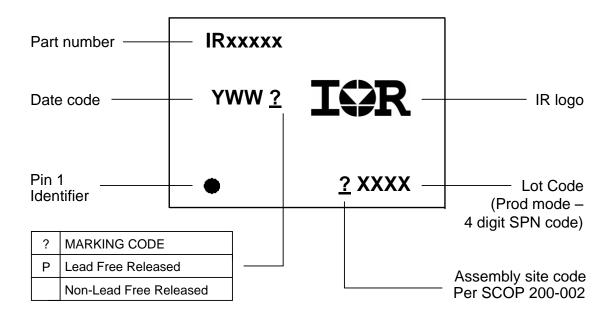


REEL DIMENSIONS FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
Α	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
B C	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566



Part Marking Information





Qualification Information[†]

4444				
	Industrial ^{††}			
	(per JEDEC JESD 47)			
Qualification Level	Comments: This family of ICs has passed JEDEC			
	Industrial qualification. IR's Consumer qualification level i			
	granted by extension of the higher Industrial level.			
	MSL2 ^{†††}			
Moisture Sensitivity Level	SOIC8N (per IPC/JEDEC J-STD 020)			
moisture ochishivity Level	Not applicable			
	PDIP8 (non-surface mount package style)			
RoHS Compliant	Yes			

- Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- Higher qualification ratings may be available should the user have such requirements. Please contact your †† International Rectifier sales representative for further information.
- ††† Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

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WORLD HEADQUARTERS:

233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

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